

Figure 1 XPS survey of 100 cycles of CdTe ALD on HgCdTe device layer, confirming presence of CdTe

Detail of in-situ spectroscopic ellipsometry thickness versus time model CdTe ALD on silicon substrate at 115 °C

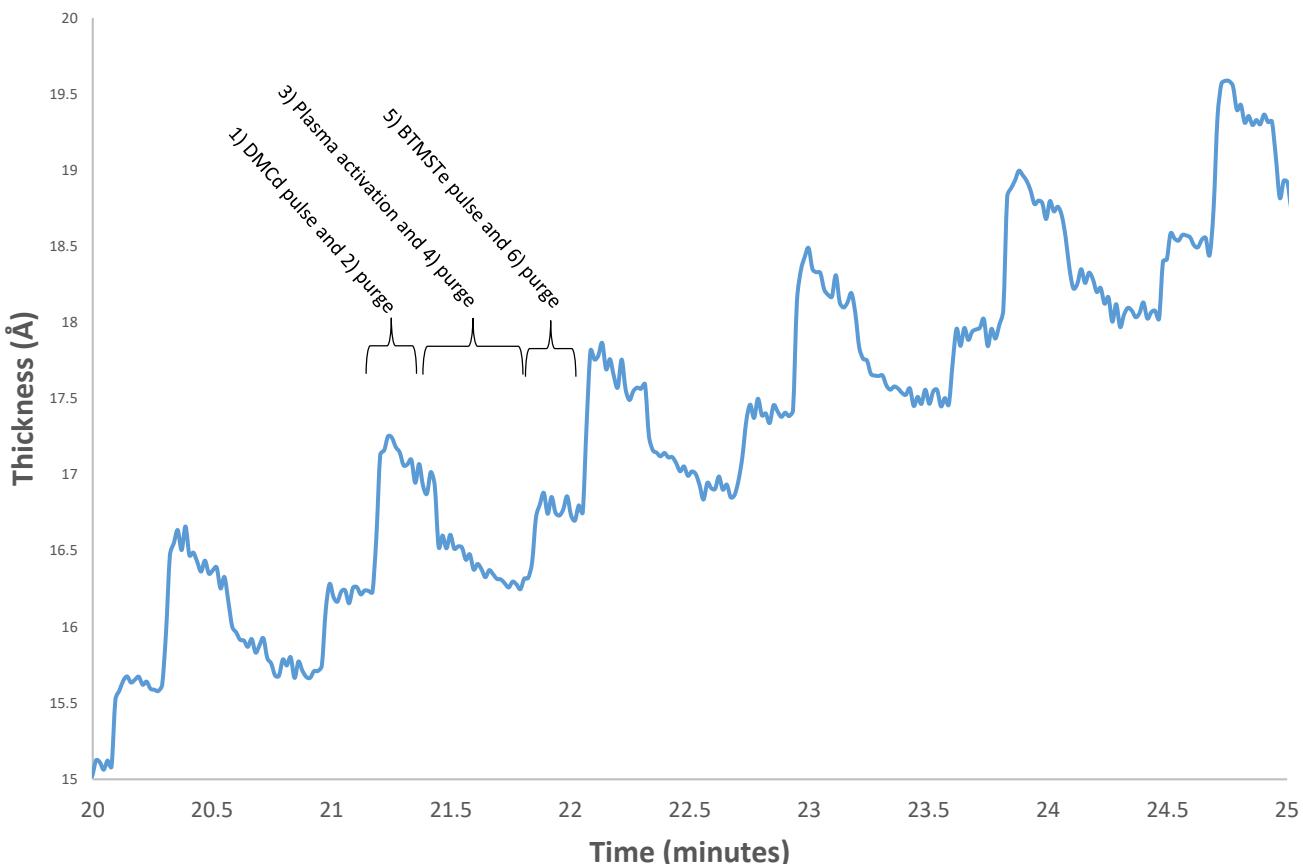


Figure 2 Dynamic in-situ spectroscopic ellipsometry of CdTe ALD on silicon substrate, indicating layer-by-layer growth